# PEMH14; PUMH14

## NPN/NPN resistor-equipped transistors;

R1 = 47 kΩ, R2 = open

Rev. 02 — 29 April 2005

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/NPN Resistor-Equipped Transistors (RET).

Table 1: Product overview

Type number				PNP/PNP	
	Philips	JEITA	complement	complement	
PEMH14	SOT666	-	PEMD14	PEMB14	
PUMH14	SOT363	SC-88	PUMD14	PUMB14	

#### 1.2 Features

- Built-in bias resistor
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	$k\Omega$



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### 2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		R1
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	

### 3. Ordering information

Table 4: Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMH14	-	plastic surface mounted package; 6 leads	SOT666	
PUMH14	SC-88	plastic surface mounted package; 6 leads	SOT363	

### 4. Marking

Table 5: Marking codes

Type number	Marking code [1]
PEMH14	5C
PUMH14	H1*

<sup>[1] \* = -:</sup> made in Hong Kong

2 of 8

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### 5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
Io	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] -	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		[1] -	300	mW
	SOT666		[1][2]	300	mW

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		[1][2]	-	625	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1] -	-	416	K/W
	SOT666		[1][2] _	-	416	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

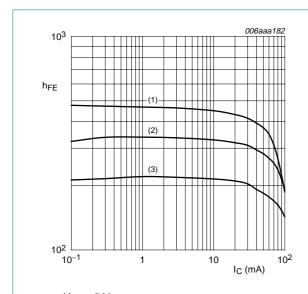
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

### 7. Characteristics

**Table 8: Characteristics** 

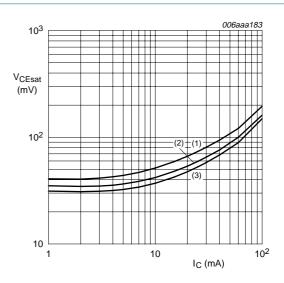
T<sub>amb</sub> = 25 °C unless otherwise specified.

· arrib – 20	C diffess offici wise spe					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		33	47	61	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF



- $V_{CE} = 5 V$
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



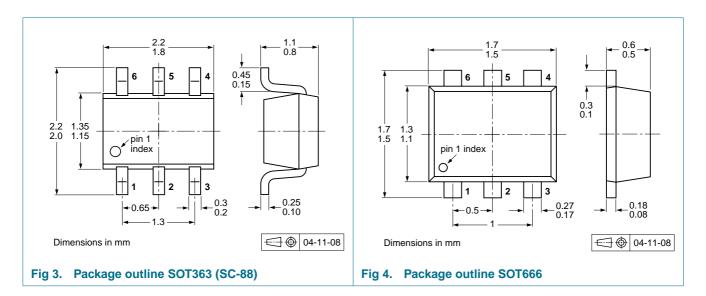
- $I_{\rm C}/I_{\rm B} = 20$
- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

**Product data sheet** 

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### 8. Package outline



### 9. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. 4

Type number	Package	Description		Packing quantity			
			3	3000	4000	8000	10000
PEMH14	SOT666	2 mm pitch, 8 mm tape and reel	-		-	-315	-
		4 mm pitch, 8 mm tape and reel	-		-115	-	-
PUMH14	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2] _	115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3] _	125	-	-	-165

[1] For further information and the availability of packing methods, see  $\underline{\text{Section 15}}$ .

[2] T1: normal taping

[3] T2: reverse taping



### 10. Revision history

#### Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PEMH14_PUMH14_2	20050429	Product data sheet	-	9397 750 14463	PUMH14_1
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new presentation ar information standard of Philips Semiconductors.</li> <li>Type PEMH14 added</li> </ul>				ew presentation and
	• Figure 1 and 2: added				
	<ul> <li>Section 9 "</li> </ul>	Packing information": a	dded		
	<ul> <li>Section 14</li> </ul>	"Trademarks": added			
PUMH14_1	20031016	Product specification	-	9397 750 11877	-

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Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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### 16. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 4
8	Package outline 5
9	Packing information 5
10	Revision history6
11	Data sheet status
12	Definitions 7
13	Disclaimers 7
14	Trademarks 7
15	Contact information

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